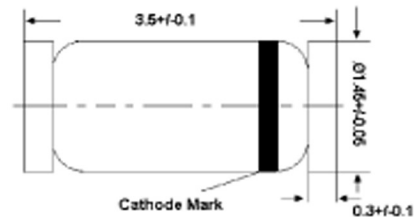


BAV100~BAV103

SILICON EPITAXIAL PLANAR DIODES

Features

- Small – signal diodes
- For general purpose



Glass case MiniMELF

Weight approx.0.05g
Dimensions in mm

Absolute Maximum Ratings ($T_s = 25^\circ\text{C}$)

	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
BAV100		100	
BAV101		150	
BAV103		200	
Repetitive Peak Reverse Voltage	V_{RRM}	60	V
BAV100		120	
BAV101		200	
BAV103		250	
Forward DC Current at $T_{amb}=25^\circ\text{C}$	I_F	250 ¹⁾	mA
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb}=25^\circ\text{C}$ and $f \geq 50\text{Hz}$	$I_{F(AV)}$	200 ¹⁾	mA
Repetitive Peak Forward Current at $T_{amb}=25^\circ\text{C}$, $f \geq 50\text{Hz}$ and $\theta=180^\circ$	I_{FRM}	625 ¹⁾	mA
Surge Forward Current at $t < 1\text{s}$ and $T_j=25^\circ\text{C}$	I_{FSM}	1000	mA
Power Dissipation	P_{tot}	400 ¹⁾	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	375	$^\circ\text{C/W}$
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to +175	$^\circ\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature.